Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3597	device ti. and(second adj dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11-13:50
L2	2948	1 and(first adj dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 13:50
L3.	87	2 and(through adj via\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 13:51
L4	7	361/311 and(electrostatic adj chuck)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 14:11
L5	72	thin adj film adj capacitor.ti. and .!'438"/\$7.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 14:52
L6	22	thin adj film adj capacitor.ti. and 361/306.3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 14:52
L7	38	thin adj film adj capacitor ti. and 361/311	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 14:52
L8	51	thin adj film adj capacitor.ti. and 361/313	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 14:52

L9	8	7 and(second adj dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 14:53
L10	13.	8 and(second adj dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 14:53
S1	623	barrier adj layer with high adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2005/05/10 09:09
S2	242	S1 with electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 09:10
S3	118	S2 and(insulat\$3 adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 09:11
S4	115	S3 and(semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 09:26
S5		361/303 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/10 10:08
S6	2	"6731496",pn.	US-PGPUB; USPAT; USOGR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:38

S7	2	361/321.2 and(electrostatic adj chuck)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:40
S9 	472	"361"/\$7.ccls. and(electrostatic adj chuck)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:41
S10	352	S9 and(substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:41
S11	346	S10 and(electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:41
<b>S12</b>	40	S11 and(dielectric adj film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:42
S13	412	Hiramatsu adj yasuji.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:43
S14	226	S13 and(ceramic adj substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:43
S15	56	S14 and(electrode and dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 10:52

S16	59	array with capacitor.ti. and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:30
S17	18	He adj jiangqi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:32
<b>S1</b> 8	0	jiangqi adj he.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:33
<b>S</b> 19	2	361/301.3 and(high adj k adj material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:37
<b>S</b> 20	10	361/303 and(high adj k adj material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:35
S21:	192	thin adj film adj capacitor:ti. and "361"/\$7.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:45
<b>S2</b> 2	9	361/301.4 and(high adj k adj material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:38
S23	10	361/303 and(high adj k adj material)	US-PGPUB; USPAT; USOGR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:38

S24	8	361/306.2 and(high adj k adj material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:41
S25	126	high adj speed adj differential adj signal\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:43
<b>S</b> 26	265	device.ti. and(high adj k adj material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 11:43
S28	168	thin adj film adj capacitor.ti. and "257"/\$7:ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 13:49